

Supplementary Materials

Incommensurate modulations and thickness-dependent energy storage density in (PbLaSrBa)(ZrSnTi)O₃ relaxor antiferroelectric thick-film ceramics

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Supplementary Table 1 Original data extracted from the references for fitting of the thickness dependences of DBS, $P_{\max}$, and W_{rec}

No.	Material type	Thickness (μm)	DBS (kV/cm)	$P_{\max}$ ($\mu\text{C}/\text{cm}^2$)	W_{rec} (J/cm^3)	Applied E-Field (kV/cm)	Ref.
1	Bulk	80	496	37	7.9	510	[1]
2	Thick film	33	412	45	14.3	530	[2]
3	Thick film	27	1082.16	53	15.79	1072.1	[3]
4	Thick film	60	717	50	14.5	717	[4]
5	Thick film	30	607.9	35	10.2	560	[5]
6	Bulk	150	690	60	12.2	680	[6]
7	Thick film	11.27	1246.5	28	11.09	1200	[7]
8	Bulk	80	325	28	6.24	290	[8]
9	Bulk	100	400	52	13	400	[9]
10	Bulk	60-70	345	40	7.152	327	[10]
11	Thick film	25–30	734	41	13.56	680	[11]
12	Thick film	45	563	41	11.4	563	[12]
13	Thick film	40	500	30	6.8	500	[13]
14	Bulk	60–80	995	63	18.5	910	[14]
15	Bulk	80	412	29	5.19	430	[15]
16	Bulk	80	387	31	4.9	400	[16]
17	Bulk	100	405	31	5.03	380	[17]
18	Bulk	70	401	38	6.387	402	[18]
19	Bulk	120	518	49	6.6	510	[19]

20	Thin film	1	2800	45	24.9	2800	[20]
21	Thin film	0.5	3294	71	49.7	3000	[21]
22	Thin film	0.3	2787	63	50.2	2800	[22]
23	Thin film	0.4	2745	35	32.4	2745	[23]
24	Thin film	0.5	2230	110	50.6	2230	[24]
25	Thin film	0.5	1800	70	32.7	1800	[25]
26	Thin film	0.6	1050	100	24.7	1050	[26]
27	Thin film	0.7	1760	77	21.1	1777	[27]
28	Thin film	0.4	4500	115	85	4500	[28]
29	Thin film	-	4500	35	46	4500	[29]
30	Thin film	-	4700	38	52	4700	[30]
31	Thin film	1.8	3700	80	56	3700	[31]
32	Thin film	0.62	6350	-	182	6350	[32]
33	Thin film	0.28-0.31	7000	88	202	7000	[33]
34	Thin film	0.65	5200	-	152	5200	[34]
35	Thin film	0.3	5920	110	133.3	5920	[35]
36	Thin film	0.45-0.5	5300	-	112	5000	[36]
37	Thin film	0.1	7400	99.7	215.8	7400	[37]
38	Thin film	-	5610	-	191.7	5610	[38]
39	Thin film	0.34	5510	-	189	5510	[39]

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